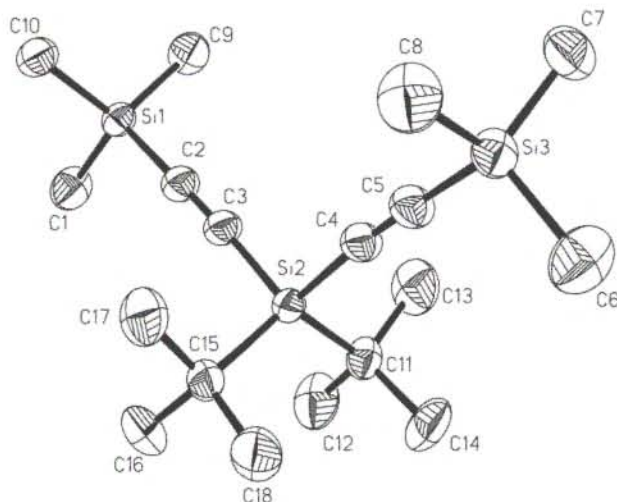


Crystal structure of di-*tert*-butylbis(3-trimethylsilylethynyl)silane, $(C_4H_9)_2Si[C_2Si(CH_3)_3]_2$

K. Peters^{*I}, E.-M. Peters^I, L. Kirmaier^{II}, D. Ostendorf^{II} and M. Weidenbruch^{II}^I Max-Planck-Institut für Festkörperforschung, Heisenbergstraße 1, D-70506 Stuttgart, Germany^{II} Universität Oldenburg, Fachbereich Chemie, Carl-von-Ossietzky-Straße 9-11, D-26111 Oldenburg, Germany

Received April 15, 1999, CCDC-No. 1267/166

**Table 1.** Data collection and handling.

Crystal:	colourless plate, size $1.2 \times 1.0 \times 0.3$ mm
Wavelength:	Mo $K\alpha$ radiation (0.71073 Å)
μ :	1.90 cm ⁻¹
Diffractometer, scan mode:	Bruker AXS P4, ω
$2\theta_{\max}$:	55°
$N(hkl)_{\text{measured}}, N(hkl)_{\text{unique}}$:	6035, 5546
Criterion for $F_{\text{obs}}, N(hkl)_{\text{gt}}$:	$F_{\text{obs}} > 3 \sigma(F_{\text{obs}})$, 3924
$N(\text{param})_{\text{refined}}$:	190
Program:	SHELXTL-plus [3]

Table 2. Atomic coordinates and displacement parameters (in Å²).

Atom	Site	x	y	z	U_{iso}
H(1A)	8f	-0.0708(1)	-0.3171(4)	0.6489(2)	0.08
H(1B)	8f	-0.0486(1)	-0.1820(4)	0.6947(2)	0.08
H(1C)	8f	-0.0144(1)	-0.3178(4)	0.6809(2)	0.08
H(6A)	8f	0.2563(1)	0.6265(4)	0.5253(2)	0.08
H(6B)	8f	0.2658(1)	0.4751(4)	0.5662(2)	0.08
H(6C)	8f	0.2356(1)	0.6081(4)	0.5918(2)	0.08
H(7A)	8f	0.2088(1)	0.4401(4)	0.4038(2)	0.08
H(7B)	8f	0.1654(1)	0.3273(4)	0.4107(2)	0.08
H(7C)	8f	0.2197(1)	0.2916(4)	0.4464(2)	0.08
H(8A)	8f	0.1497(1)	0.6963(4)	0.4538(2)	0.08
H(8B)	8f	0.1312(1)	0.6774(4)	0.5219(2)	0.08
H(8C)	8f	0.1073(1)	0.5797(4)	0.4606(2)	0.08
H(9A)	8f	-0.0399(1)	-0.3518(3)	0.5113(2)	0.08
H(9B)	8f	0.0159(1)	-0.3528(3)	0.5465(2)	0.08
H(9C)	8f	-0.0021(1)	-0.2345(3)	0.4901(2)	0.08
H(10A)	8f	-0.1076(1)	-0.0851(3)	0.5381(1)	0.08
H(10B)	8f	-0.0693(1)	0.0297(3)	0.5164(1)	0.08
H(10C)	8f	-0.0852(1)	0.0459(3)	0.5862(1)	0.08
H(12A)	8f	0.1514(1)	-0.0189(4)	0.7942(2)	0.08
H(12B)	8f	0.1832(1)	-0.1532(4)	0.7730(2)	0.08
H(12C)	8f	0.1271(1)	-0.1367(4)	0.7408(2)	0.08
H(13A)	8f	0.1897(1)	-0.0229(4)	0.6120(2)	0.08
H(13B)	8f	0.1504(1)	-0.1394(4)	0.6298(2)	0.08
H(13C)	8f	0.2065(1)	-0.1559(4)	0.6620(2)	0.08
H(14A)	8f	0.2156(1)	0.1638(4)	0.7667(2)	0.08
H(14B)	8f	0.2302(1)	0.1594(4)	0.6958(2)	0.08
H(14C)	8f	0.2457(1)	0.0251(4)	0.7456(2)	0.08
H(16A)	8f	0.1057(1)	0.1742(4)	0.8097(2)	0.08
H(16B)	8f	0.0524(1)	0.1691(4)	0.7668(2)	0.08
H(16C)	8f	0.0693(1)	0.3122(4)	0.8108(2)	0.08
H(17A)	8f	0.0326(1)	0.3347(4)	0.6674(2)	0.08
H(17B)	8f	0.0724(1)	0.4494(4)	0.6497(2)	0.08
H(17C)	8f	0.0483(1)	0.4761(4)	0.7131(2)	0.08
H(18A)	8f	0.1692(1)	0.3557(4)	0.7795(2)	0.08
H(18B)	8f	0.1314(1)	0.4895(4)	0.7811(2)	0.08
H(18C)	8f	0.1555(1)	0.4628(4)	0.7178(2)	0.08

Abstract

$C_{18}H_{36}Si_3$, monoclinic, $C12/c1$ (No. 15), $a = 27.284(2)$ Å, $b = 8.769(1)$ Å, $c = 20.467(2)$ Å, $\beta = 99.75(1)^\circ$, $V = 4826.1$ Å³, $Z = 8$, $R_{\text{gt}}(F) = 0.059$, $wR(F) = 0.057$, $T = 293$ K.

Source of material

Photolysis of hexa-*tert*-butylcyclotrisilane or 1,1-di-*tert*-butyl-*trans*-2,3-dimethylsilirane in the presence of 1,4-bis(trimethylsilyl)buta-1,3-diyne furnishes the title compound [1].

Discussion

The crystal structure analysis reveals a distorted tetrahedral environment of the middle silicon atom. The most conspicuous features are the short Si–C bond lengths to the acetylenic carbon atoms of 184.4(2) pm and 185.2(3) pm and the considerable widened C–Si–C bond angle of $119.7(1)^\circ$ within the $^t\text{Bu}_2\text{Si}$ moiety [2].

* Correspondence author

(e-mail: karpet@vsibml.mpi-stuttgart.mpg.de)

Table 3. Atomic coordinates and displacement parameters (in Å²).

Atom	Site	<i>x</i>	<i>y</i>	<i>z</i>	<i>U</i> ₁₁	<i>U</i> ₂₂	<i>U</i> ₃₃	<i>U</i> ₁₂	<i>U</i> ₁₃	<i>U</i> ₂₃
Si(1)	8 <i>f</i>	−0.02664(2)	−0.15231(8)	0.58919(3)	0.0481(4)	0.0539(4)	0.0582(4)	−0.0054(3)	0.0031(3)	−0.0029(3)
Si(2)	8 <i>f</i>	0.12083(2)	0.15682(8)	0.66944(3)	0.0419(3)	0.0546(4)	0.0468(4)	−0.0053(3)	0.0075(3)	0.0001(3)
Si(3)	8 <i>f</i>	0.18411(3)	0.47532(9)	0.50689(4)	0.0707(5)	0.0676(5)	0.0695(5)	−0.0014(4)	0.0171(4)	0.0195(4)
C(1)	8 <i>f</i>	−0.0420(1)	−0.2546(4)	0.6622(2)	0.074(2)	0.100(2)	0.093(2)	−0.005(2)	0.013(2)	0.025(2)
C(2)	8 <i>f</i>	0.0292(1)	−0.0337(3)	0.6178(1)	0.057(1)	0.066(2)	0.058(1)	−0.006(1)	0.007(1)	−0.002(1)
C(3)	8 <i>f</i>	0.06531(9)	0.0434(3)	0.6361(1)	0.054(1)	0.066(2)	0.053(1)	−0.008(1)	0.005(1)	−0.002(1)
C(4)	8 <i>f</i>	0.14303(9)	0.2619(3)	0.6016(1)	0.062(2)	0.067(2)	0.055(1)	−0.010(1)	0.009(1)	0.002(1)
C(5)	8 <i>f</i>	0.1593(1)	0.3408(3)	0.5629(1)	0.071(2)	0.070(2)	0.059(2)	−0.008(1)	0.014(1)	0.004(1)
C(6)	8 <i>f</i>	0.2425(1)	0.5560(4)	0.5531(2)	0.106(3)	0.092(3)	0.140(3)	−0.025(2)	0.005(2)	0.024(2)
C(7)	8 <i>f</i>	0.1959(1)	0.3711(4)	0.4331(2)	0.101(3)	0.138(3)	0.078(2)	0.017(2)	0.031(2)	0.022(2)
C(8)	8 <i>f</i>	0.1375(1)	0.6251(4)	0.4829(2)	0.117(3)	0.095(3)	0.129(3)	0.020(2)	0.024(3)	0.028(2)
C(9)	8 <i>f</i>	−0.0113(1)	−0.2894(3)	0.5268(2)	0.080(2)	0.071(2)	0.094(2)	−0.000(2)	0.007(2)	−0.018(2)
C(10)	8 <i>f</i>	−0.0784(1)	−0.0251(3)	0.5531(1)	0.069(2)	0.075(2)	0.073(2)	0.004(2)	−0.000(1)	−0.006(2)
C(11)	8 <i>f</i>	0.17158(9)	0.0171(3)	0.7039(1)	0.056(2)	0.070(2)	0.075(2)	0.007(1)	0.013(1)	0.009(1)
C(12)	8 <i>f</i>	0.1570(1)	−0.0820(4)	0.7579(2)	0.095(3)	0.111(3)	0.128(3)	0.031(2)	0.022(2)	0.050(3)
C(13)	8 <i>f</i>	0.1803(1)	−0.0847(4)	0.6466(2)	0.103(3)	0.097(3)	0.141(3)	0.037(2)	0.026(2)	−0.007(3)
C(14)	8 <i>f</i>	0.2203(1)	0.0989(4)	0.7305(2)	0.055(2)	0.125(3)	0.136(3)	0.015(2)	−0.010(2)	−0.001(3)
C(15)	8 <i>f</i>	0.10035(9)	0.3069(3)	0.7257(1)	0.055(1)	0.069(2)	0.067(2)	0.001(1)	0.014(1)	−0.015(1)
C(16)	8 <i>f</i>	0.0800(1)	0.2338(4)	0.7837(2)	0.110(3)	0.122(3)	0.079(2)	0.008(2)	0.043(2)	−0.014(2)
C(17)	8 <i>f</i>	0.0597(1)	0.4003(4)	0.6853(2)	0.095(2)	0.094(2)	0.120(3)	0.031(2)	0.023(2)	−0.011(2)
C(18)	8 <i>f</i>	0.1431(1)	0.4137(4)	0.7536(2)	0.096(3)	0.109(3)	0.132(3)	−0.016(2)	0.028(2)	−0.062(3)

References

1. Kirmaier, L.: Reaktionen von Silylenen und Disilenen mit einigen 1,3-Dienen und 1,3-Diinen. Dissertation, Universität Oldenburg, Germany 1998.
2. Lukevics, E.; Pudova, O.; Sturkovich, R.: Molecular Structure of Organosilicon Compounds, Ellis Horwood, Chichester, UK 1989.
3. Sheldrick, G. M.: Program Package SHELXTL-plus. Release 4.1. Siemens Analytical X-Ray Instruments Inc., Madison (WI 53719), USA 1990.